

CLAIMS

What is claimed is:

- 1 1. A method for manufacturing a magnetic structure on a magnetic write head,
2 comprising:
3 constructing a photoresist layer having a trench;
4 depositing a magnetic material into the trench;
5 removing the photoresist layer;
6 depositing a dielectric material;
7 performing a chemical mechanical polish to remove a portion of said dielectric
8 material;
9 performing a reactive ion mill procedure to remove a sufficient amount of
10 dielectric material to expose said magnetic material.
- 1 2. A method as in claim 1 further comprising forming a magnetic pole structure over
2 the exposed magnetic material.
- 1 3. A method as in claim 1 wherein said constructing a photoresist trench further
2 comprises:
3 depositing photoresist; and
4 performing a deep ultraviolet photolithography on the photoresist.

1 4. A method as in claim 1, wherein said depositing said magnetic material comprises
2 electroplating.

1 5. A method as in claim 1, wherein said depositing said magnetic material comprises
2 electroplating said magnetic material, and terminating said electroplating before said
3 magnetic material reaches an upper opening in said trench formed in said photoresist
4 layer.

6. A method as in claim 1, wherein said trench includes a flared portion, and
wherein said depositing said magnetic material comprises electroplating said magnetic
material, and terminating said electroplating before said magnetic material reaches said
flared portion formed in said trench.

1 7 A method as in claim 1, wherein said magnetic material comprises NiFe.

1 8. A method as in claim 2, wherein said magnetic pole structure comprises NiFe.

1 9. A method as in claim 1, wherein said reactive ion milling procedure is performed
2 sufficiently to form a recession of between 0 and 0.3 microns between said magnetic
3 structure and an upper surface of said alumina.

1 10. A method as in claim 1 wherein said magnetic structure has a width sigma of less
2 than 10 nanometers.

1 12. A method as in claim 1 wherein said trench formed in said photoresist layer has a
2 width sigma of less than 10 nanometers up to a location where said magnetic
3 material deposition will terminate.

1 13. A method as in claim 1 wherein said dielectric material is alumina (Al_2O_3).

1 14. A method as in claim 1 wherein said magnetic structure is a P3 pedestal of a
2 magnetic pole.

1 15. A method as in claim 1 wherein said reactive ion mill is performed in an
2 atmosphere comprising CHF_3 .

1 16. A method as in claim 1 wherein said reactive ion mill is performed sufficiently to
2 create a recess between an upper surface of said magnetic structure and an upper
3 surface of said dielectric material.

1 17. A method as in claim 1 wherein said reactive ion mill is performed sufficiently to
2 create a recess between an upper surface of said magnetic layer and an upper surface of
3 said dielectric layer wherein said recess is between .1 and .3 microns inclusive.

1 18. A method as in claim 1 wherein said reactive ion mill is performed sufficiently to
2 create a recess between an upper surface of said magnetic layer and an upper surface of
3 said dielectric layer wherein said recess is about .3 microns.

1 19. A structure formed on a magnetic write head, comprising:
2 a magnetic structure having an upper surface and having first and second lateral
3 sides and having a width measured between said lateral sides and having a height
4 measured perpendicular thereto;
5 a dielectric layer contacting said first and second lateral sides of said magnetic
6 structure and extending laterally therefrom and having an upper surface; and
7 wherein
8 said upper surface of said dielectric layer is recessed from said upper surface of
9 said magnetic structure and said upper surface of said dielectric layer.

1 20. A structure as in claim 19 wherein said recess is between .1 and .5 microns.

1 21. A structure as in claim 19 wherein said recess is about .3 microns.